

#### P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(th)</sub> < 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- **ESD Protected Gate**
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

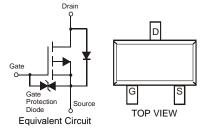
### **Mechanical Data**

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

SOT-323



TOP VIEW



# Maximum Ratings @T<sub>A</sub> = 25℃ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Drain Current (Note 1)	ΙD	-400	mA
Pulsed Drain Current	I <sub>DM</sub>	-1.4	А

## Thermal Characteristics @T<sub>A</sub> = 25℃ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_d$	250	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	500	€/M
Operating and Storage Temperature Range	$T_{j},T_{STG}$	-55 to +150	C

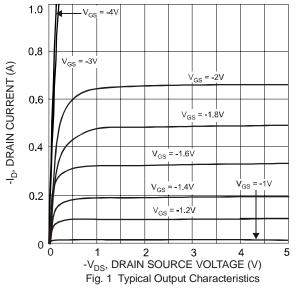
## Electrical Characteristics @TA = 25°C unless otherwise specified

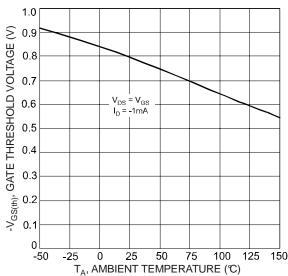
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_{D} = -250mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±1.0	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 4)	ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			0.7	0.9		$V_{GS} = -4.5V$ , $I_D = -430mA$	
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	1.1	1.4	Ω	$V_{GS} = -2.5V, I_D = -300mA$	
			1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$	
Forward Transfer Admittance	Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = 10V, I_{D} = -0.2A$	
Diode Forward Voltage (Note 4)	$V_{SD}$	-0.5	_	-1.2	V	$V_{GS} = 0V, I_{S} = -115mA$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>iss</sub>		_	175	pF	101/11/101/	
Output Capacitance	Coss	_		30	pF	$V_{DS} = -16V, V_{GS} = 0V$ - f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		_	20	pF	1 = 1.0IVII 12	

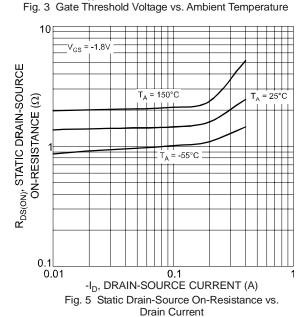
Notes:

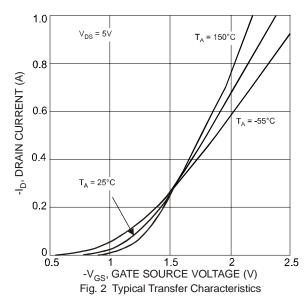
- Device mounted on FR-4 PCB.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php. Short duration pulse test used to minimize self-heating effect.











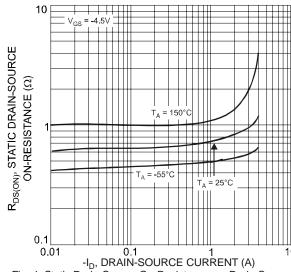


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

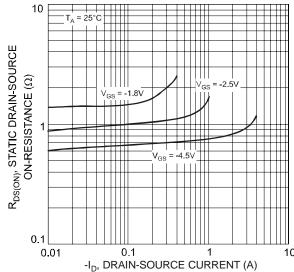


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage



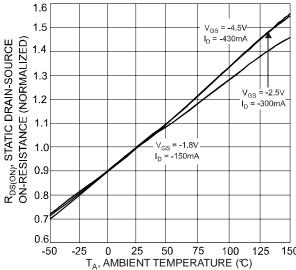


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

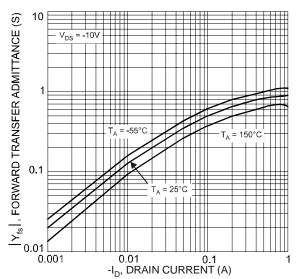


Fig. 9 Forward Transfer Admittance vs. Drain Current

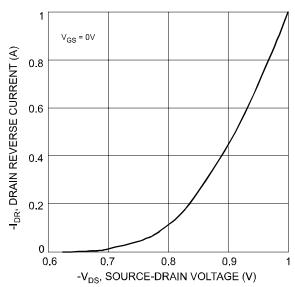
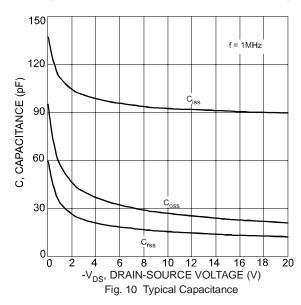


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage

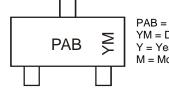


# Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2004WK-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



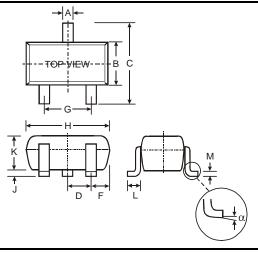
PAB = Product Type Marking Code YM = Date Code Marking Y = Year ex: U = 2007 M = Month ex: 9 = September

Date Code Key

Year	20	07	20	08	20	09	20	10	20	11	20	12
Code	Ų	J	\	/	V	V	)	(	`	1	Ž	<u> </u>
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

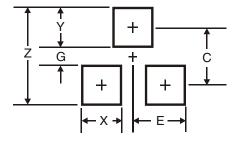


# **Package Outline Dimensions**



SOT-323					
Dim	Min	Max			
Α	0.25	0.40			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 N	0.65 Nominal			
F	0.30	0.40			
G	1.20	1.40			
Н	1.80	2.20			
J	0.0	0.10			
K	0.90	1.00			
L	0.25	0.40			
M	0.10	0.18			
α	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.8
G	1.0
Х	0.7
Υ	0.9
С	1.9
Е	0.65

#### IMPORTANT NOTICE

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